

WHAT IS CLAIMED IS:

1. A manufacturing apparatus of a buried insulating layer-type semiconductor silicon carbide substrate, comprising: a heating furnace in which an SOI substrate having a surface silicon layer of a predetermined thickness and having a buried insulator is placed and which has a heating means for heating the SOI substrate; and a gas supply means for supplying a variety of gases into this heating furnace, characterized in that said gas supply means can supply, at least, a hydrogen gas, a hydrocarbon gas, an oxygen gas, an inert gas and a silane-based gas into the heating furnace.

2. The manufacturing apparatus of a buried insulating layer-type semiconductor silicon carbide substrate, characterized in that the inside of said heating furnace is at atmospheric pressure.